

INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.
FIS9-2001-0 295-US2

SERIAL NO. Divisional of
10/047,964

Tze-Chiang Chen et al.

FILING 8-29-03
8/27/03

GROUP

5250 2825

10-650890

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CL	6,043,152	03/28/2000	Chang et al.			
	6,080,529	06/27/2000	Ye et al.			
	6,099,701	08/08/2000	Liu et al.			
	6,107,188	08/22/2000	Liu et al.			
	6,127,238	10/03/2000	Liao et al.			
	6,153,523	11/28/2000	Van Ngo et al.			
	6,162,583	12/19/2000	Yang et al.			
	6,211,061 B1	04/03/2001	Chen et al.			
	6,218,732 B1	04/17/2001	Russell et al.			
	6,225,210 B1	05/01/2001	Ngo et al.			
CL	6,235,633 B1	05/22/2001	Jang			

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
CL ✓	WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
	✓ JP2001015480A	01/19/2001	Japan				
	✓ JP2001053076A	02/23/2001	Japan				
	✓ JP1111843A	04/28/1989	Japan				
CL	WO 99/33102	07/01/1999	JP,KR, European Patent				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CL	J	Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
CL	✓	R.D. Goldblatt et al., "A High Performance 0.13 um Copper BEOL Technology with Low-k Dielectric," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 261-263, June 5-7, 2000.

EXAMINER

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DATE CONSIDERED

7.26.04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Tze-Chiang Chen et al.

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8-27-03

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5350

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>CL</u>	6,261,951 B1	07/17/2001	Buchwalter et al.	—	—	
	US 2001/0000155 A1	04/05/2001	Huang et al.	—	—	
	US 2001/0002333 A1	05/31/2001	Huang et al.	—	—	
	US 2001/0002731 A1	06/07/2001	Ueda	—	—	
	US 2001/0003064 A1	06/07/2001	Ohto	—	—	
	6,265,779	07/24/01	Grill, et al.	—	—	
<u>CL</u>	6,441,491	08/27/02	Grill, et al.	—	—	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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<u>CL</u>	<input checked="" type="checkbox"/>	J. Yota et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 76-78, June 5-7, 2000.

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